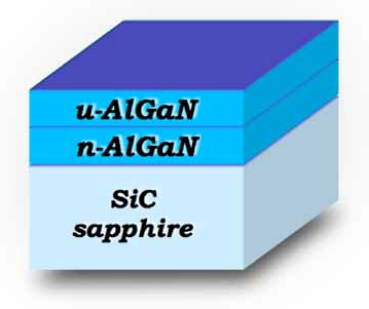
UV Sensor

UV-Sensor Epi-Wafer

Typical Epi Structure

Epi-Layer	Size	Thickness	Dopant	Concentration	Al, In Content
Undoped AlInGaN Layer	---	---	none	---	*1
n-AlInGaN Layer	---	---	Si	---	*1
Nucleation Layer	---	---	---	---	---
Substrate *2	2inch, 3inch, 100mm,,,	---	---	---	---

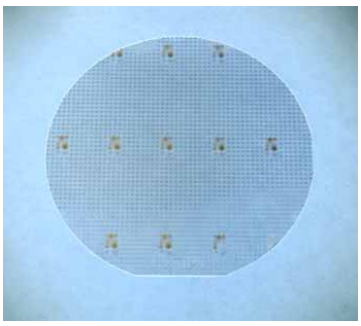
*1 Depending on the Cut-off WaveLength
*2 SiC, sapphire



Typical Characteristics

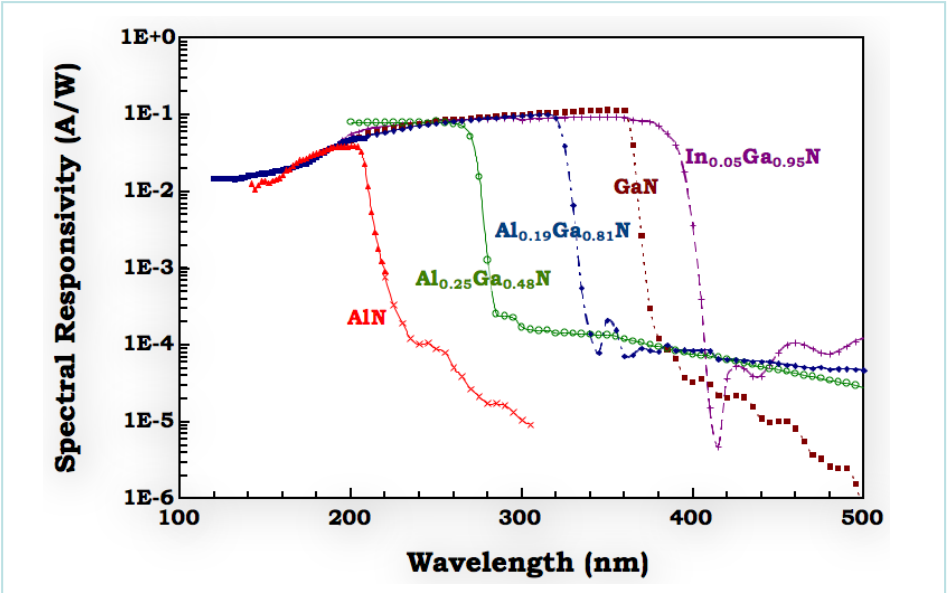
Cut-off WaveLength	200～400nm
Responsivity (peak)	100mA/W

Wafer



UV-Sensor Device

Spectral Responsivity [1), 2)]



1) T. Saito, T. Hitora, H. Hitora, H. Kawai, I. Saito, and E. Yamaguchi, "UV/VUV hotodetectors using Group III - Nitride Semiconductors", Phys Status Solidi C 6, S658-S661(2009).
2) T. Saito, T. Hitora, H. Ishihara, M. Matsuoka, H. Hitora, H. Kawai, I. Saito, and E. amaguchi, "Group III - Nitride Semiconductor Schottky Barrier Photodiodes for the Radiometric Use in the UV and VUV Regions", Metrologia 46, S272-S276 (2009).

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